

74LVC623A-Q100

Octal transceiver with dual enable; 3-state

Rev. 1 — 17 April 2013

Product data sheet

1. General description

The 74LVC623A-Q100 is an octal transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions. This octal bus transceiver is designed for asynchronous two-way communication between data buses.

The control function implementation allows maximum flexibility in timing. This device allows data transmission from the An bus to the Bn bus or from the Bn bus to the An bus. The data flow direction depends on the logic levels at the enable inputs (pins OEAB and OEBA). The enable inputs can be used to disable the device so that the buses are effectively isolated. The dual enable function configuration gives this transceiver the capability to store data by simultaneous enabling of pins OEAB and OEBA. Each output reinforces its input in this transceiver configuration. Thus, when both control inputs are enabled and all other data sources to the two sets of the bus lines are at high-impedance OFF-state, both sets of the bus lines remain at their last states. The 8-bit codes on the two sets of buses are identical.

Inputs can be driven from either 3.3 V or 5 V devices. When disabled, up to 5.5 V can be applied to the outputs. These features allow the use of these devices as translators in mixed 3.3 V or 5 V applications.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40°C to $+85^{\circ}\text{C}$ and from -40°C to $+125^{\circ}\text{C}$
- 5 V tolerant inputs and outputs for interfacing with 5 V logic
- Wide supply voltage range from 1.2 V to 3.6 V
- CMOS low power consumption
- Direct interface with TTL levels
- High-impedance when $V_{CC} = 0\text{ V}$
- Complies with JEDEC standard:
 - ◆ JESD8-7A (1.65 V to 1.95 V)
 - ◆ JESD8-5A (2.3 V to 2.7 V)
 - ◆ JESD8-C/JESD36 (2.7 V to 3.6 V)
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\ \Omega$)

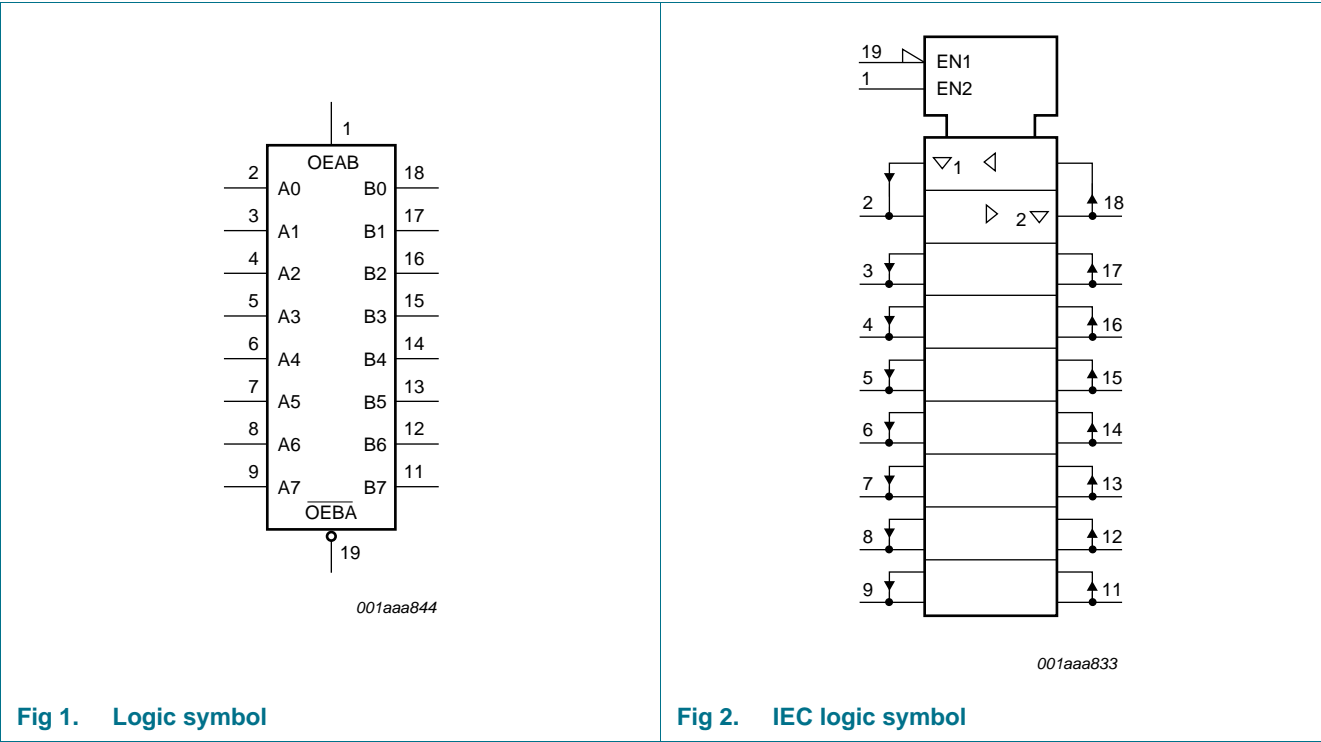


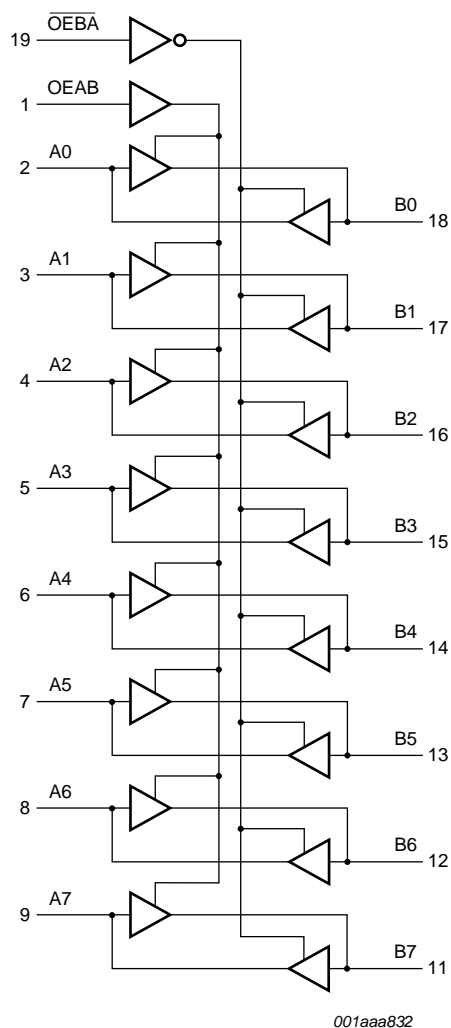
3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC623AD-Q100	−40 °C to +125 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74LVC623ADB-Q100	−40 °C to +125 °C	SSOP20	plastic shrink small outline package; 20 leads; body width 5.3 mm	SOT339-1
74LVC623APW-Q100	−40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1

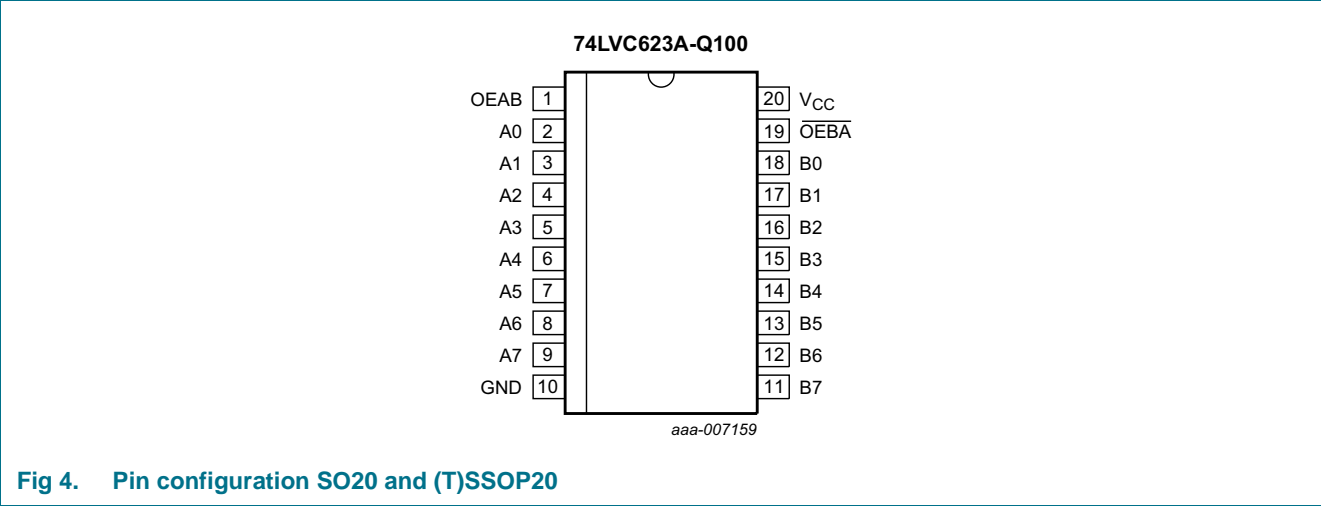
4. Functional diagram



**Fig 3. Logic diagram**

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Pin	Symbol	Description
1	OEAB	output enable input
19	$\overline{\text{OEBA}}$	output enable input (active LOW)
A[0:7]	2, 3, 4, 5, 6, 7, 8, 9	data input or output
B[0:7]	18, 17, 16, 15, 14, 13, 12, 11	data output or input
10	GND	ground (0 V)
20	V _{CC}	supply voltage

6. Functional description

Table 3. Function table^[1]

Input		Input or output	
OEAB	OEBA	An	Bn
L	L	An = Bn	input
H	H	input	Bn = An
L	H	Z	Z
H	L	An = Bn	input
		input	Bn = An

[1] H = HIGH voltage level; L = LOW voltage level; Z = high-impedance OFF-state

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
V _I	input voltage		^[1] -0.5	+6.5	V
V _O	output voltage	HIGH or LOW state	^[2] -0.5	V _{CC} + 0.5	V
		3-state	^[2] -0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
I _{OK}	output clamping current	V _O > V _{CC} or V _O < 0 V	-	±50	mA
I _O	output current	V _O = 0 V to V _{CC}	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	±150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	^[3] -	500	mW

[1] The minimum input voltage ratings may be exceeded if the input current ratings are observed.

[2] The output voltage ratings may be exceeded if the output current ratings are observed.

[3] For SO20 package: above 70 °C P_{tot} derates linearly with 8 mW/K.
For (T)SSOP20 packages: above 60 °C P_{tot} derates linearly with 5.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CC}	supply voltage		1.65	-	3.6	V
		functional	1.2	-	-	V
V _I	input voltage		0	-	5.5	V
V _O	output voltage	HIGH or LOW state	0	-	V _{CC}	V
		3-state or V _{CC} = 0 V	0	-	5.5	V
T _{amb}	ambient temperature	in free air	-40	-	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 1.65 V to 2.7 V	0	-	20	ns/V
		V _{CC} = 2.7 V to 3.6 V	0	-	10	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V _{IH}	HIGH-level input voltage	V _{CC} = 1.2 V	1.08	-	-	1.08	-	V
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}	-	-	0.65 × V _{CC}	-	V
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.2 V	-	-	0.12	-	0.12	V
		V _{CC} = 1.65 V to 1.95 V	-	-	0.35 × V _{CC}	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = -100 μA; V _{CC} = 1.65 V to 3.6 V	V _{CC} - 0.2	-	-	V _{CC} - 0.3	-	V
		I _O = -4 mA; V _{CC} = 1.65 V	1.2	-	-	1.05	-	V
		I _O = -8 mA; V _{CC} = 2.3 V	1.8	-	-	1.65	-	V
		I _O = -12 mA; V _{CC} = 2.7 V	2.2	-	-	2.05	-	V
		I _O = -18 mA; V _{CC} = 3.0 V	2.4	-	-	2.25	-	V
		I _O = -24 mA; V _{CC} = 3.0 V	2.2	-	-	2.0	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = 100 μA; V _{CC} = 1.65 V to 3.6 V	-	-	0.2	-	0.3	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.45	-	0.65	V
		I _O = 8 mA; V _{CC} = 2.3 V	-	-	0.6	-	0.8	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.4	-	0.6	V
		I _O = 24 mA; V _{CC} = 3.0 V	-	-	0.55	-	0.8	V
I _I	input leakage current	V _{CC} = 3.6 V; V _I = 5.5 V or GND	-	±0.1	±5	-	±20	μA

Table 6. Static characteristics ...continued

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _{CC} = 3.6 V; V _O = 5.5 V or GND; [2]	-	0.1	±5	-	±20	μA
I _{OFF}	power-off leakage current	V _{CC} = 0 V; V _I or V _O = 5.5 V	-	0.1	±10	-	±20	μA
I _{CC}	supply current	V _{CC} = 3.6 V; V _I = V _{CC} or GND; I _O = 0 A	-	0.1	10	-	40	μA
ΔI _{CC}	additional supply current	per input pin; V _{CC} = 2.7 V to 3.6 V; V _I = V _{CC} - 0.6 V; I _O = 0 A	-	5	500	-	5000	μA
C _I	input capacitance	V _{CC} = 0 V to 3.6 V; V _I = GND to V _{CC}	-	4.0	-	-	-	pF
C _{I/O}	input/output capacitance	V _{CC} = 0 V to 3.6 V; V _I = GND to V _{CC}	-	10.0	-	-	-	pF

[1] All typical values are measured at V_{CC} = 3.3 V (unless stated otherwise) and T_{amb} = 25 °C.[2] For transceivers, the parameter I_{OZ} includes the input leakage current.

10. Dynamic characteristics

Table 7. Dynamic characteristicsVoltages are referenced to GND (ground = 0 V). For test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t _{pd}	propagation delay	An to Bn; Bn to An; see Figure 5 [2]						
		V _{CC} = 1.2 V	-	19	-	-	-	ns
		V _{CC} = 1.65 V to 1.95 V	1.7	6.4	13.5	1.7	14.2	ns
		V _{CC} = 2.3 V to 2.7 V	1.5	3.4	6.7	1.5	7.4	ns
		V _{CC} = 2.7 V	1.5	3.4	5.7	1.5	7.5	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	2.9	5.2	1.0	6.5	ns
t _{en}	enable time	OEAB to Bn; see Figure 6 [2]						
		V _{CC} = 1.2 V	-	26	-	-	-	ns
		V _{CC} = 1.65 V to 1.95 V	2.7	8.7	17.0	2.7	17.9	ns
		V _{CC} = 2.3 V to 2.7 V	2.2	4.8	8.9	2.2	9.8	ns
		V _{CC} = 2.7 V	1.5	4.2	6.9	1.5	9.0	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	3.9	6.6	1.0	8.5	ns
		OEBA to An; see Figure 7 [2]						
		V _{CC} = 1.2 V	-	26	-	-	-	ns
		V _{CC} = 1.65 V to 1.95 V	2.6	8.1	17.0	2.6	17.9	ns
		V _{CC} = 2.3 V to 2.7 V	2.2	4.5	8.9	2.2	9.8	ns
		V _{CC} = 2.7 V	1.5	4.6	7.5	1.5	9.5	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	3.6	6.6	1.0	8.5	ns

Table 7. Dynamic characteristics ...continuedVoltages are referenced to GND (ground = 0 V). For test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t_{dis}	disable time	OEAB to Bn; see Figure 6 ^[2]						
		$V_{CC} = 1.2\text{ V}$	-	12	-	-	-	ns
		$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	2.3	4.7	10.5	2.3	11.1	ns
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	1.0	2.6	5.7	1.0	6.4	ns
		$V_{CC} = 2.7\text{ V}$	1.5	4.2	6.2	1.5	8.0	ns
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$	1.0	3.2	5.5	1.0	7.0	ns
	OEBA to An; see Figure 7 ^[2]	$V_{CC} = 1.2\text{ V}$	-	11	-	-	-	ns
		$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	3.6	5.2	10.1	3.6	10.7	ns
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	1.0	2.9	5.5	1.0	6.1	ns
		$V_{CC} = 2.7\text{ V}$	1.5	3.7	5.5	1.5	7.0	ns
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$	1.0	3.4	5.3	1.0	7.0	ns
	output skew time	$V_{CC} = 3.0\text{ V to }3.6\text{ V}$ ^[3]	-	-	1.0	-	1.5	ns
C_{PD}	power dissipation capacitance	per input; $V_I = \text{GND to }V_{CC}$ ^[4]						
		$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	-	11.9	-	-	-	pF
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	-	15.5	-	-	-	pF
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$	-	18.8	-	-	-	pF

[1] Typical values are measured at $T_{amb} = 25\text{ °C}$ and $V_{CC} = 1.2\text{ V}, 1.8\text{ V}, 2.5\text{ V}, 2.7\text{ V}$, and 3.3 V respectively.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .
 t_{en} is the same as t_{PZL} and t_{PZH} .
 t_{dis} is the same as t_{PLZ} and t_{PHZ} .

[3] Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz; f_o = output frequency in MHz

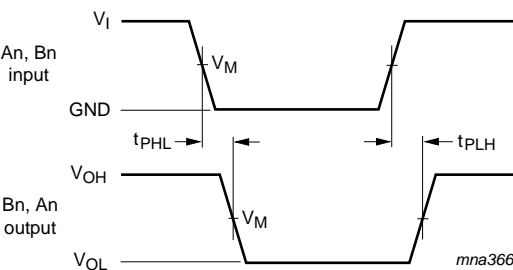
C_L = output load capacitance in pF

V_{CC} = supply voltage in Volts

N = number of inputs switching

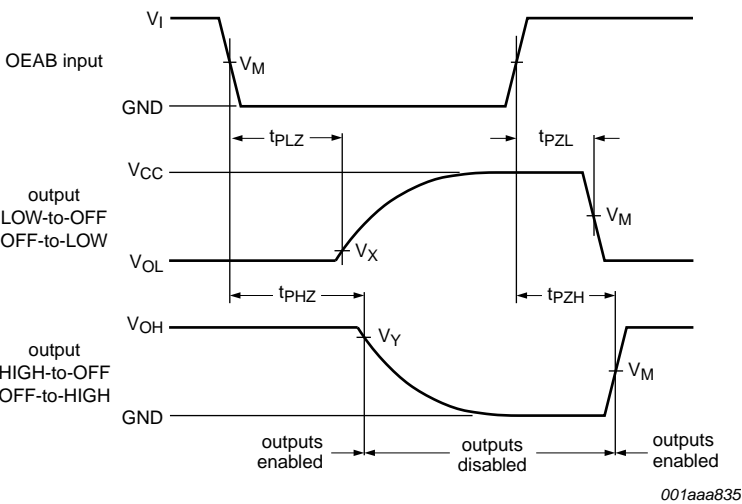
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs

11. Waveforms



$V_M = 1.5\text{ V}$ at $V_{CC} \geq 2.7\text{ V}$;
 $V_M = 0.5 \times V_{CC}$ at $V_{CC} < 2.7\text{ V}$.
 V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 5. The inputs An, Bn to outputs Bn, An propagation delays

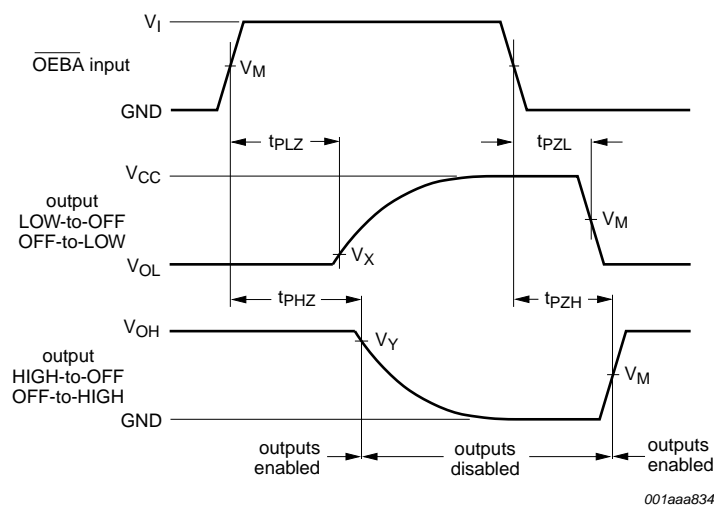


Measurement points are given in [Table 8](#).
 V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 6. 3-state enable and disable times for OEAB input

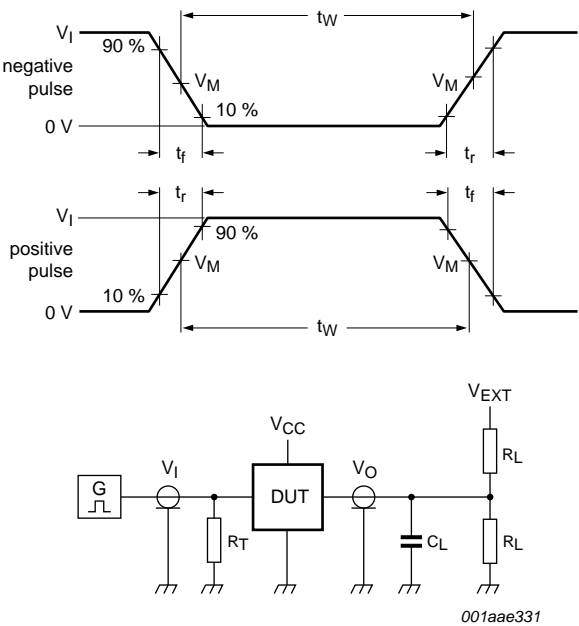
Table 8. Measurement points

Supply voltage	Input	Output		
V_{CC}	V_M	V_M	V_X	V_Y
$< 2.7\text{ V}$	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.15\text{ V}$	$V_{OH} - 0.15\text{ V}$
$\geq 2.7\text{ V}$	1.5 V	1.5 V	$V_{OL} + 0.3\text{ V}$	$V_{OH} - 0.3\text{ V}$



Measurement points are given in [Table 8](#).
 V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 7. 3-state enable and disable times for OEBA input



Test data is given in [Table 9](#).
Definitions for test circuit:
 R_L = Load resistance.
 C_L = Load capacitance including jig and probe capacitance.
 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.
 V_{EXT} = External voltage for measuring switching times.

Fig 8. Test circuit for measuring switching times

Table 9. Test data

Supply voltage	Input		Load		V _{EXT}		
	V _I	t _r , t _f	C _L	R _L	t _{PLH} , t _{PHL}	t _{PLZ} , t _{PZL}	t _{PHZ} , t _{PZH}
1.2 V	V _{CC}	≤ 2 ns	30 pF	1 kΩ	open	2 × V _{CC}	GND
1.65 V to 1.95 V	V _{CC}	≤ 2 ns	30 pF	1 kΩ	open	2 × V _{CC}	GND
2.3 V to 2.7 V	V _{CC}	≤ 2 ns	30 pF	500 Ω	open	2 × V _{CC}	GND
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	2 × V _{CC}	GND
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	2 × V _{CC}	GND

12. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1

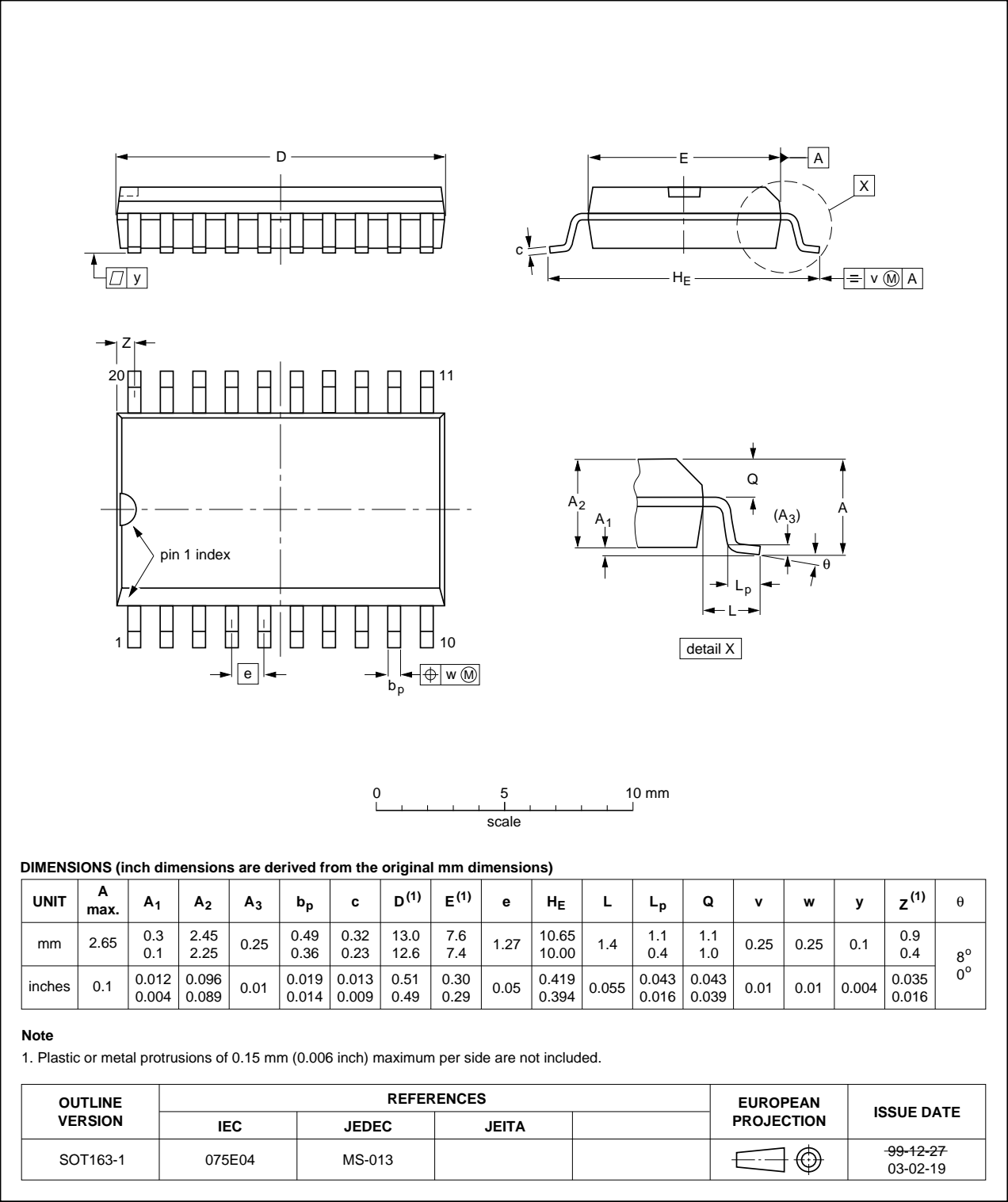


Fig 9. Package outline SOT163-1 (SO20)

SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm

SOT339-1

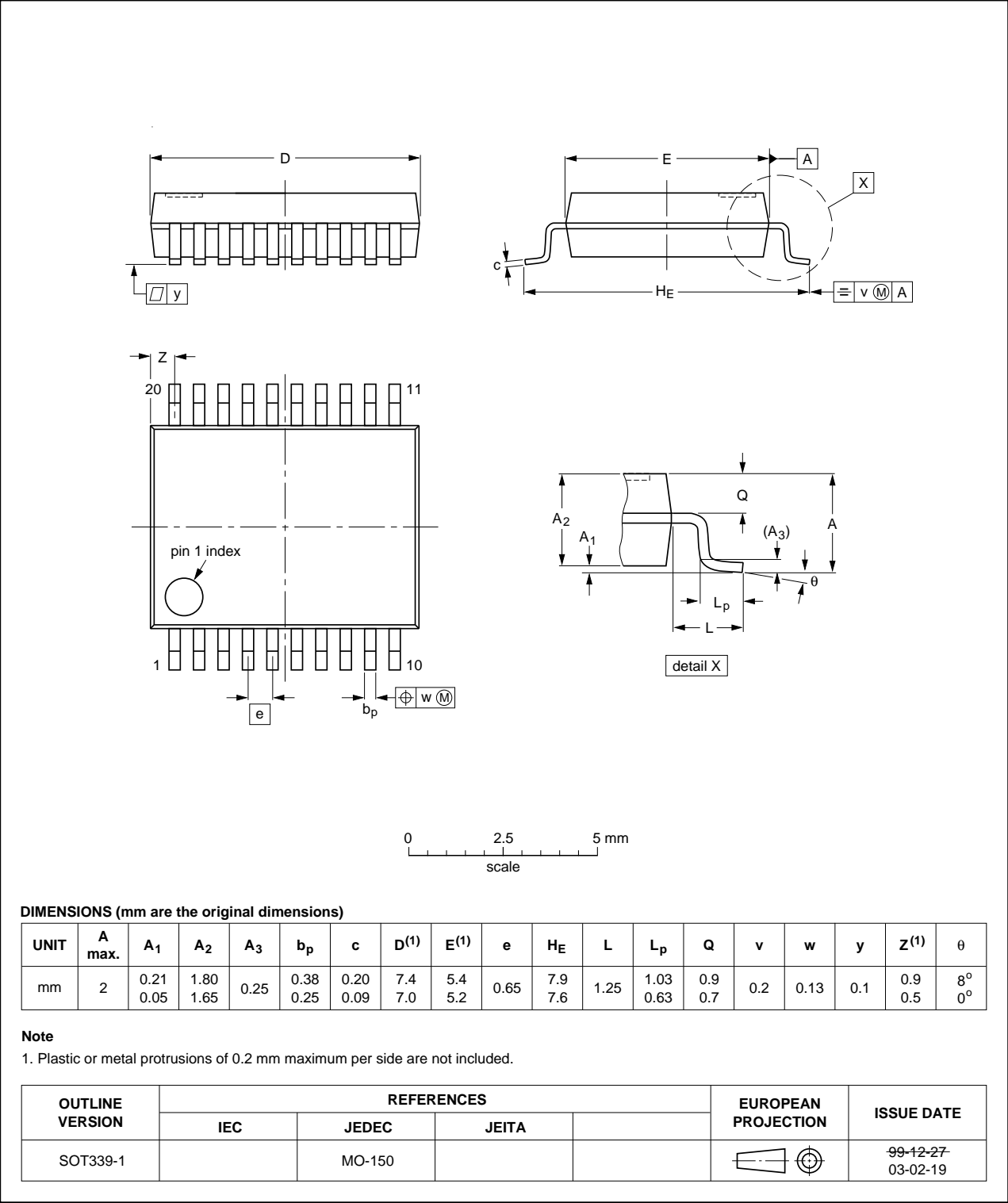


Fig 10. Package outline SOT339-1 (SSOP20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1

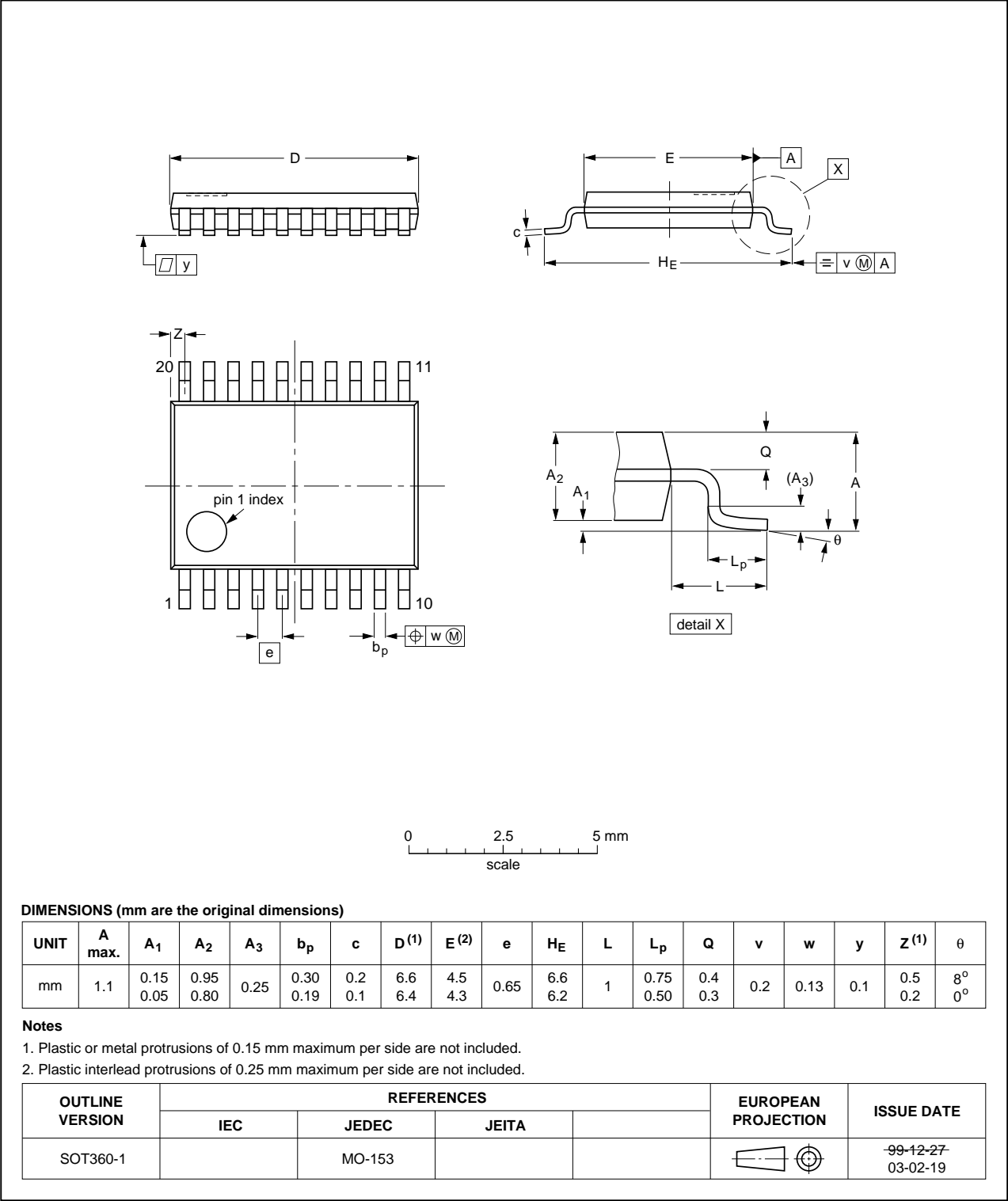


Fig 11. Package outline SOT 360-1 (TSSOP20)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC623A_Q100 v.1	20130417	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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